



## N-Channel 30-V (D-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)
30	0.035 at V <sub>GS</sub> = 10 V	7.4	4.2 nC
	0.052 at V <sub>GS</sub> = 4.5 V	6.1	

SCHOTTKY PRODUCT SUMMARY		
V <sub>KA</sub> (V)	V <sub>F</sub> (V) Diode Forward Voltage	I <sub>F</sub> (A) <sup>a</sup>
30	0.470 at 3 A	3

### FEATURES

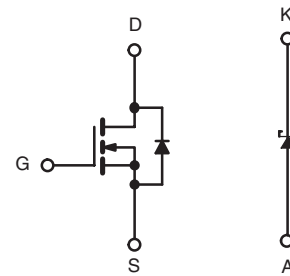
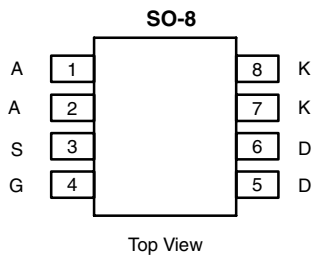
- LITTLE FOOT® Plus Power MOSFET

### APPLICATIONS

- Load Switch for Portable Applications  
- Ideal for Boost Circuits
- HDD Driver



**RoHS**  
COMPLIANT



Ordering Information: Si4620DY-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage (MOSFET)	V <sub>DS</sub>	30	V	
Reverse Voltage (Schottky)	V <sub>KA</sub>	30		
Gate-Source Voltage (MOSFET)	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) (MOSFET)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	7.5	
		T <sub>C</sub> = 70 °C	6	
		T <sub>A</sub> = 25 °C	6	
		T <sub>A</sub> = 70 °C	4.8	
Pulsed Drain Current (MOSFET)	I <sub>DM</sub>	40	A	
Continuous Source Current (MOSFET Diode Conduction)	I <sub>S</sub>	T <sub>C</sub> = 25 °C		2.6
		T <sub>A</sub> = 25 °C		1.7 <sup>a, b</sup>
Average Forward Current (Schottky)	I <sub>F</sub>	3	W	
Pulsed Forward Current (Schottky)	I <sub>FM</sub>	8		
Maximum Power Dissipation (MOSFET)	P <sub>D</sub>	T <sub>C</sub> = 25 °C		3.1
		T <sub>C</sub> = 70 °C	2	
		T <sub>A</sub> = 25 °C	2 <sup>a, b</sup>	
		T <sub>A</sub> = 70 °C	1.3 <sup>a, b</sup>	
Maximum Power Dissipation (Schottky)	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3	
		T <sub>C</sub> = 70 °C	1.9	
		T <sub>A</sub> = 25 °C	1.8	
		T <sub>A</sub> = 70 °C	1.1	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature)		260		

**THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) <sup>a, c</sup>	$R_{thJA}$	53	62.5	°C/W
Maximum Junction-to-Foot (Drain) (MOSFET)	$R_{thJF}$	30	40	
Maximum Junction-to-Ambient (Schottky)	$R_{thJA}$	55	65	
Maximum Junction-to-Foot (Drain) (Schottky)	$R_{thJF}$	32	42	

## Notes:

a. Surface Mounted on FR4 Board.

b.  $t \leq 10$  sec.

c. Maximum under Steady State conditions for MOSFETS is 110 °C/W.

d. Maximum under Steady State conditions for Schottky is 115 °C/W.

**SPECIFICATIONS**  $T_J = 25$  °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0$ V, $I_D = 250$ $\mu$ A	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ $\mu$ A		32.5		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250$ $\mu$ A	1.2		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			$\pm 100$	nS
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30$ V, $V_{GS} = 0$ V			1	$\mu$ A
		$V_{DS} = 30$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq 5$ V, $V_{GS} = 4.5$ V	40			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 6$ A		0.028	0.035	$\Omega$
		$V_{GS} = 4.5$ V, $I_D = 4.9$ A		0.041	0.052	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15$ V, $I_D = 6$ A		12		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15$ V, $V_{GS} = 0$ V, $f = 1$ MHz		520	1040	pF
Output Capacitance	$C_{oss}$			115	230	
Reverse Transfer Capacitance	$C_{rss}$			55	110	
Total Gate Charge	$Q_g$	$V_{DS} = 15$ V, $V_{GS} = 10$ V, $I_D = 6$ A		8.6	13	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15$ V, $V_{GS} = 4.5$ V, $I_D = 6$ A		4.2	6.5	
Gate-Drain Charge	$Q_{gd}$			1.8		
Gate Resistance	$R_g$	$f = 1$ MHz		2.8		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15$ V, $R_L = 3.1$ $\Omega$ $I_D \cong 4.8$ A, $V_{GEN} = 4.5$ V, $R_g = 6$ $\Omega$		16	30	ns
Rise Time	$t_r$			36	54	
Turn-Off Delay Time	$t_{d(off)}$			21	40	
Fall Time	$t_f$			17	40	



<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			2.6	A
Pulse Diode Forward Current	$I_{SM}$				40	
Body Diode Voltage	$V_{SD}$	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		20	40	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			14	30	nC
Reverse Recovery Fall Time	$t_a$			14		ns
Reverse Recovery Rise Time	$t_b$			6		

Notes:

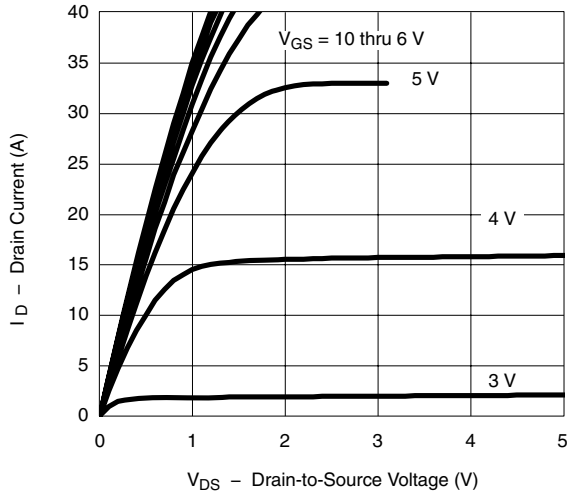
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

<b>SCHOTTKY SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage Drop	$V_F$	$I_F = 3\text{ A}$		0.39	0.470	V
		$I_F = 3\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.35	0.420	
Maximum Reverse Leakage Current	$I_{rm}$	$V_r = 5\text{ V}$		0.1	0.2	mA
		$V_r = 5\text{ V}, T_J = 85\text{ }^\circ\text{C}$		3.5	17.5	
		$V_r = 5\text{ V}, T_J = 106\text{ }^\circ\text{C}$		12	60	
		$V_r = 30\text{ V}$		0.22	0.5	
		$V_r = 30\text{ V}, T_J = 85\text{ }^\circ\text{C}$		10	50	
		$V_r = 30\text{ V}, T_J = 125\text{ }^\circ\text{C}$		40	200	
Junction Capacitance	$C_T$	$V_r = 15\text{ V}$		100		pF

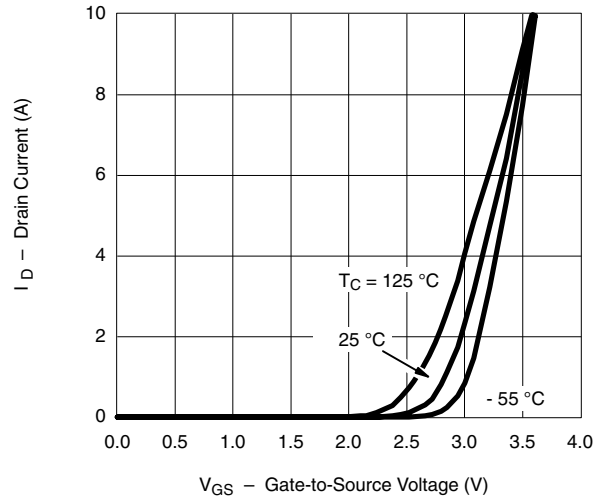
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



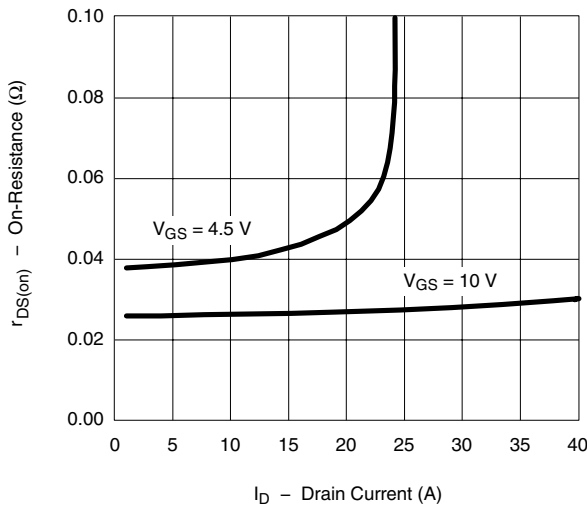
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



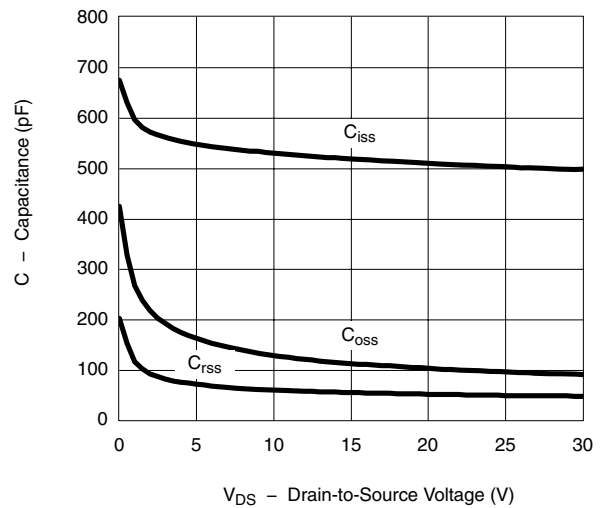
**Output Characteristics**



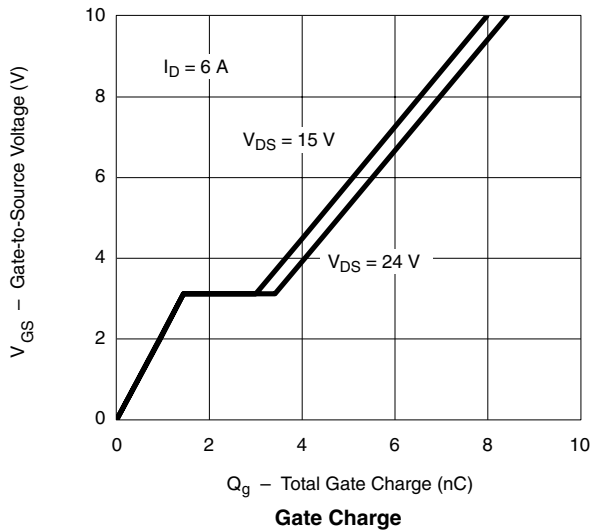
**Transfer Characteristics**



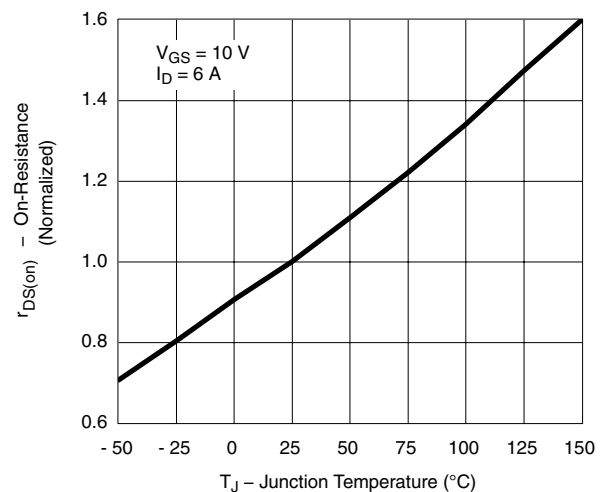
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



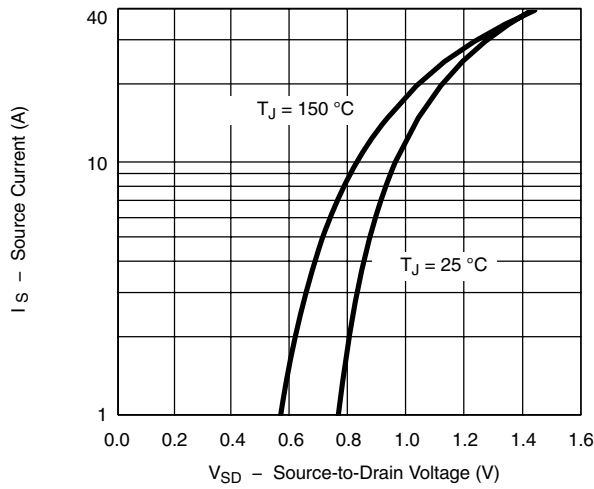
**Gate Charge**



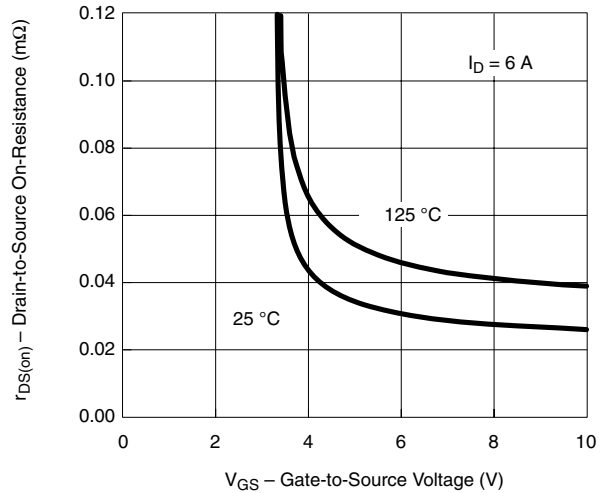
**On-Resistance vs. Junction Temperature**



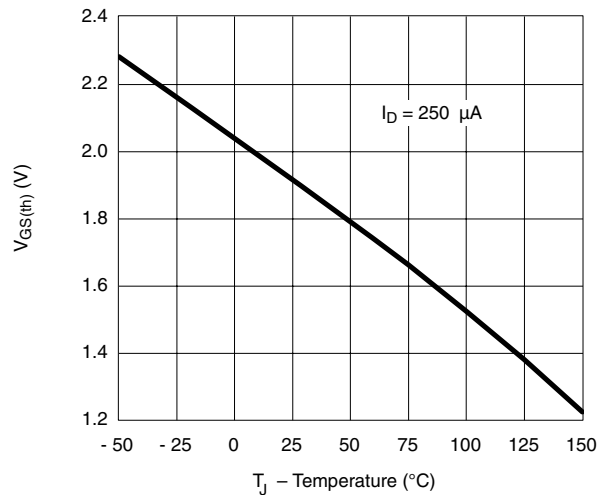
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



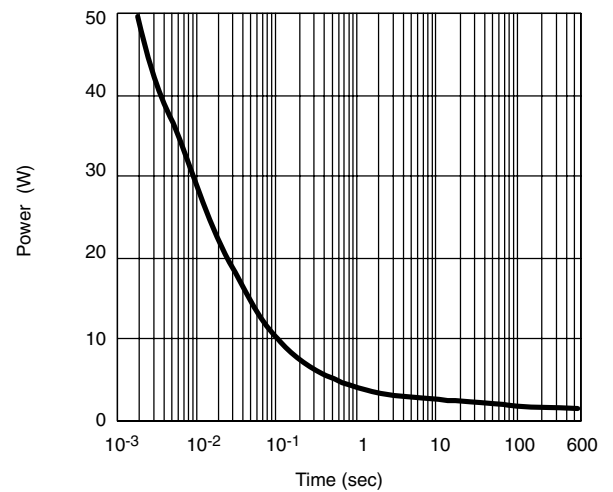
**Source-Drain Diode Forward Voltage**



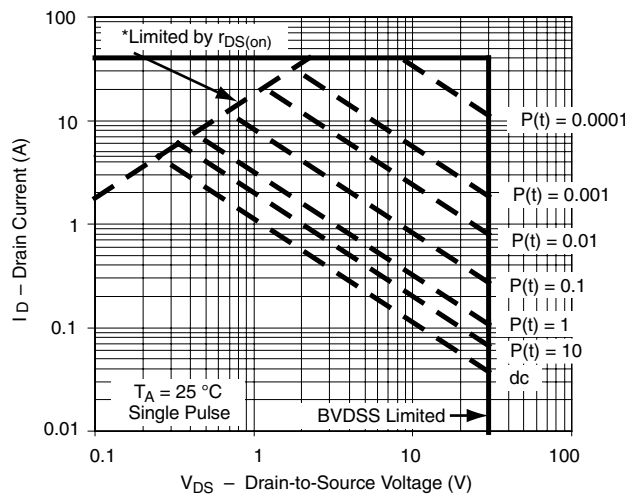
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



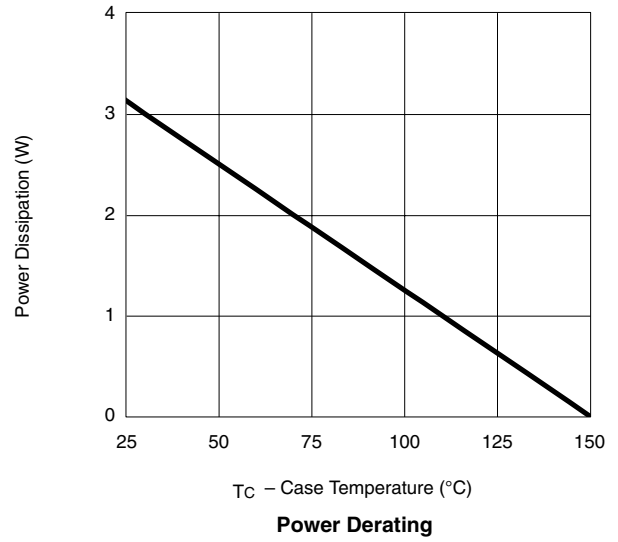
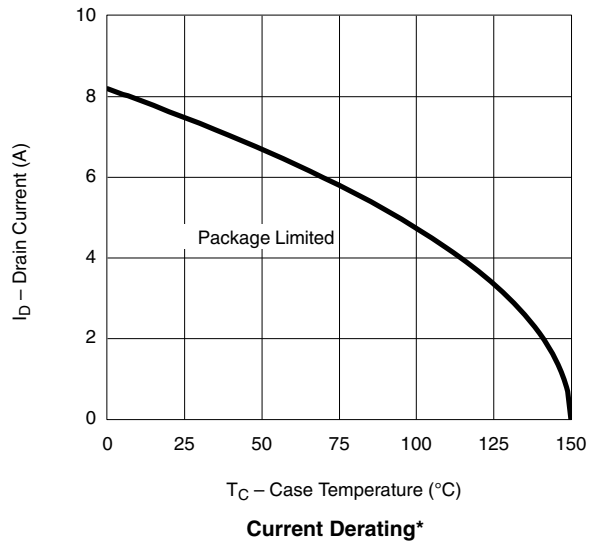
**Single Pulse Power**



\* $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified  
**Safe Operating Area, Junction-to-Ambient**



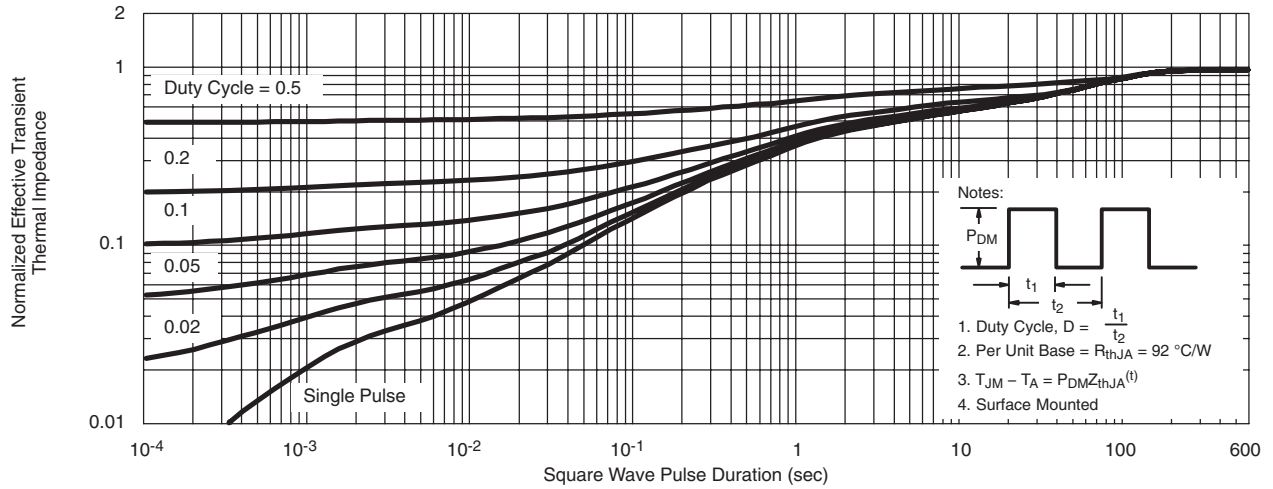
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



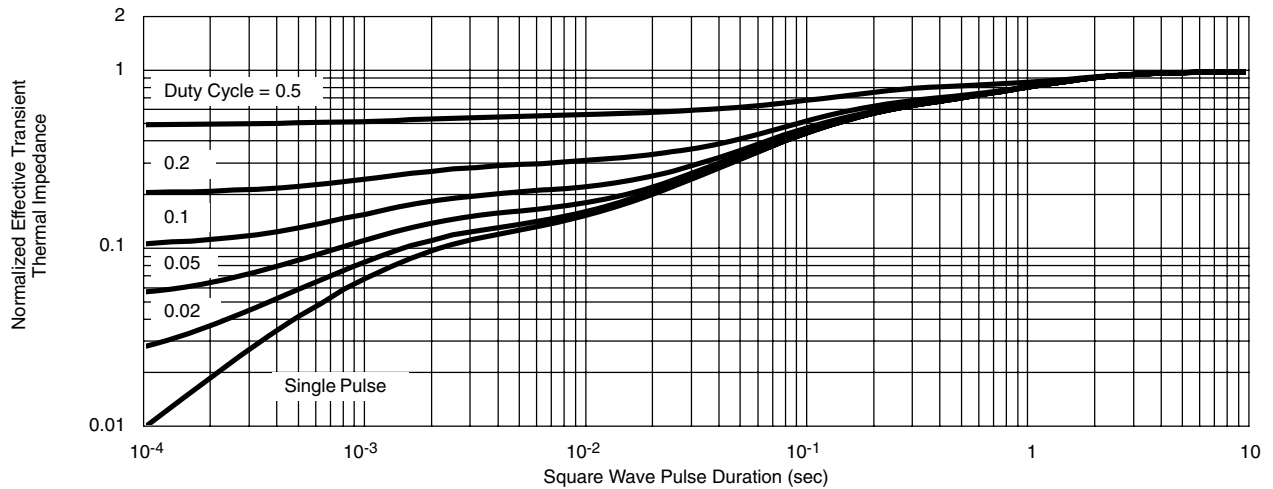
\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



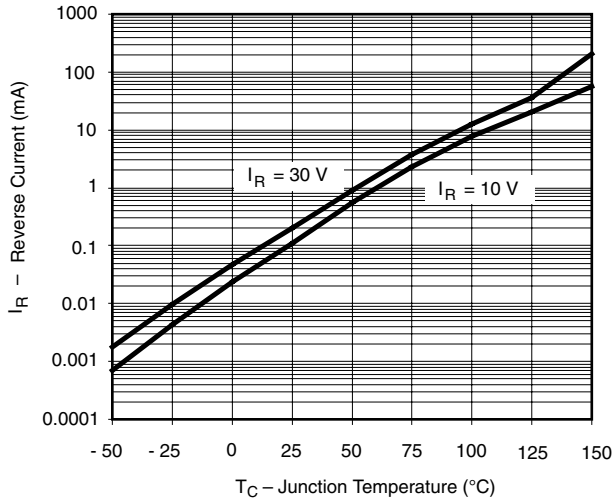
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



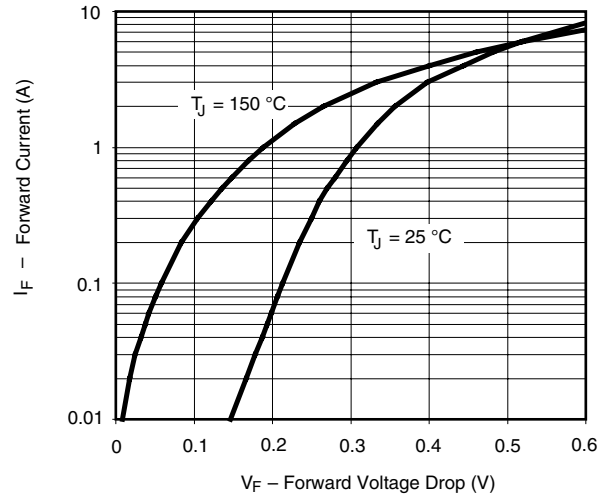
**Normalized Thermal Transient Impedance, Junction-to-Foot**



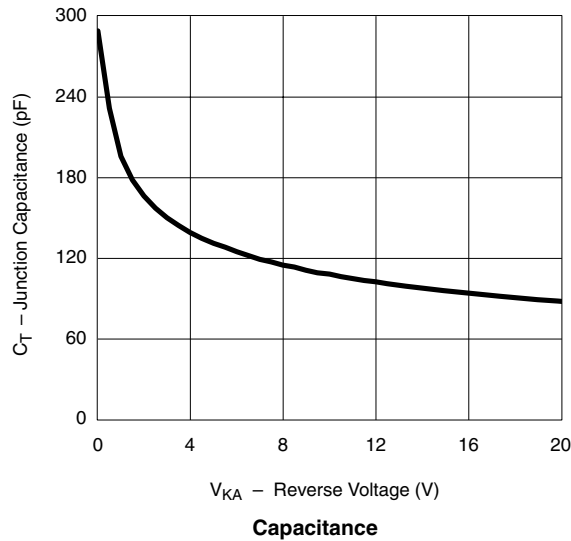
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Reverse Current vs. Junction Temperature**



**Forward Voltage Drop**

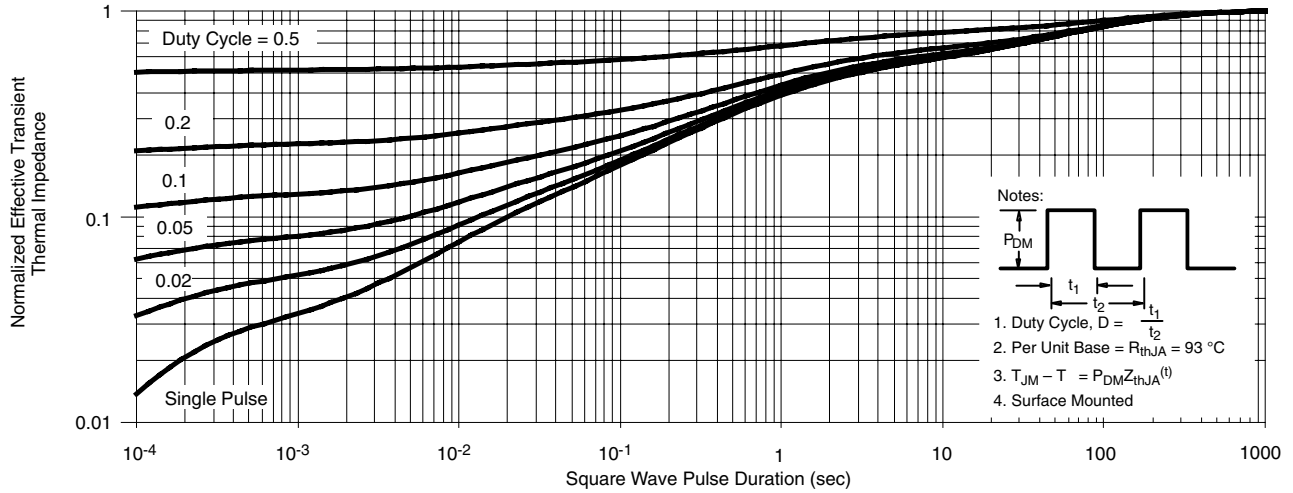


**Capacitance**

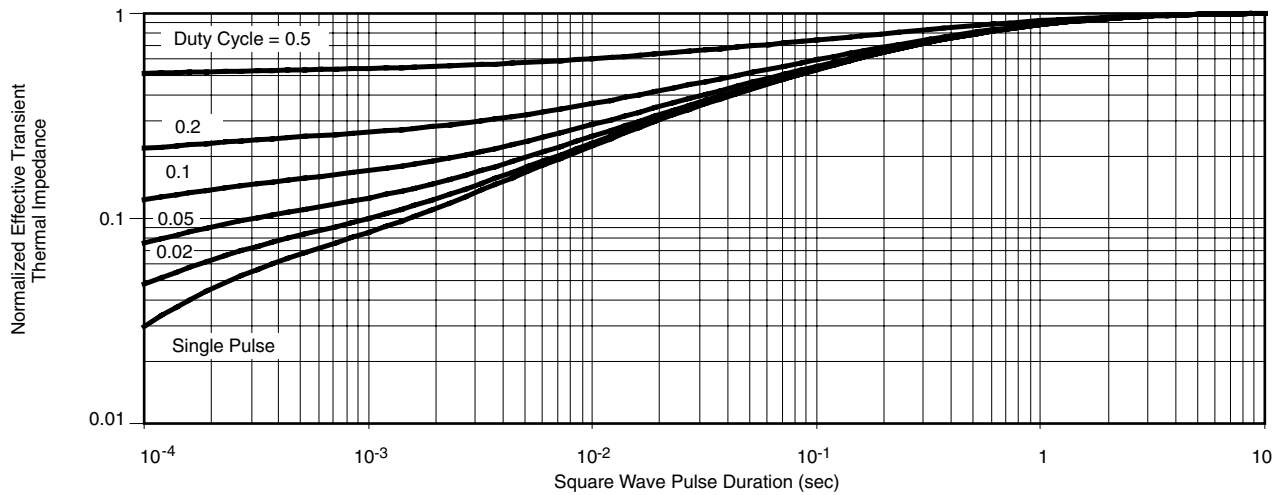




**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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